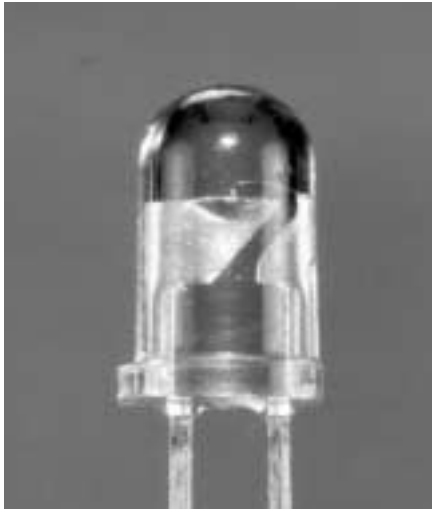


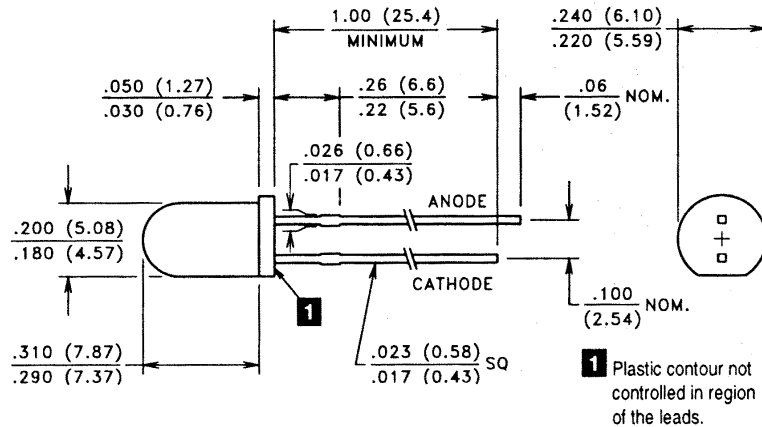
GaAlAs Infrared Emitting Diodes

T-1 $\frac{3}{4}$ (5 mm) Plastic Package — 880 nm

VTE1281W-1, W-2



PACKAGE DIMENSIONS inch (mm)



CASE 26W T-1 $\frac{3}{4}$ (5 mm) WIDE ANGLE
CHIP SIZE: .015" x .015"

DESCRIPTION

This wide beam angle 5 mm diameter plastic packaged emitter contains a GaAlAs, 880 nm IRED chip. It is a cost effective design and is well suited for high current pulse applications.

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures			
Storage and Operating:	-40°C to 100°C	Maximum Reverse Voltage:	5.0V
Continuous Power Dissipation:	200 mW	Maximum Reverse Current @ $V_R = 5V$:	10 μA
Derate above 30°C:	2.86 mW/°C	Peak Wavelength (Typical):	880 nm
Maximum Continuous Current:	100 mA	Junction Capacitance @ 0V, 1 MHz (Typ.):	23 pF
Derate above 30°C:	1.43 mA/°C	Response Time @ $I_F = 20 mA$	
Peak Forward Current, 10 μs , 100 pps:	2.5 A	Rise: 1.0 μs Fall: 1.0 μs	
Temp. Coefficient of Power Output (Typ.):	-8%/°C	Lead Soldering Temperature:	260°C
		(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output						Forward Drop		Half Power Beam Angle	
	Irradiance		Radiant Intensity	Total Power	Test Current	V_F				
	E_e	Condition		I_e	P_O	I_{FT}	@ I_{FT}	$\theta_{1/2}$		
	mW/cm ²	distance	Diameter	mW/sr	mW	mA	Volts			
	Min.	Typ.	mm	mm	Min.	Typ.	(Pulsed)	Typ.	Max.	Typ.
VTE1281W-1	1.2	1.6	36	6.4	16	20	100	1.5	2.0	$\pm 25^\circ$
VTE1281W-2	2.5	3.3	36	6.4	32	25	100	1.5	2.0	$\pm 25^\circ$

■ Refer to General Product Notes, page 2.